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Gas Sensing with Epitaxial Graphene on SiC

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Gas sensing with epitaxial graphene

- Why graphene?
- Production of epitaxial graphene on SiC
- Gas response of epitaxial graphene gas sensors
- Controlling graphene uniformity and doping
- Effect of graphene layer thickness on sensitivity to chemical gating





Why Graphene?



- Massless, pseudo-relativistic Dirac fermions
- Linear energy-momentum dispersion:
 - ✤p- bands touch at Dirac points
- > Ballistic transport at room temperature, and intrinsic mobility $\mu > 10^5$ cm² V⁻¹s⁻¹.

Why Graphene sensors?

MOMENTUM

Low density of states near the Dirac point (E_D) – small changes in the number of charge carriers results in large resistance changes
 Low noise, chemically stable, conductive even at the limit of no charge carriers





Graphene production

Graphene is produced by the high temperature sublimation of Si from SiC

> The process is carried out in Ar at 2000°C and atmospheric pressure which gives a more uniform graphene coverage

- > Growth on the Si face (0001) SiC gives more control over the number of layers than on the C face (000 \overline{I})
- > The potential of producing large-area lithography-compatible films.

> If the carriers remain ballistic, it will lead to a fascinating world of carbon based electronics.





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C. Riedl et al. PRL **103** (2009)



Graphene layers sit on a buffer or interfacial layer
The buffer layer is covalently bound to the underlying SiC
Thickness controlled by temperature

Gas response-single layer graphene





Detection limit of NO₂ < 10 ppb



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Detection limits in the low ppt and even ppq range possible for NO₂ and NO

Chen et. Al., Applied Physics Letters 101, 053119 (2012)



Gas sensing-single layer graphene



R. Pearce, et al., Sensors and Actuators B: Chemical, 155, (2011), 451-455

Graphene on SiC: n-type conductivity NO₂ consumes electrons – p-type conductivity **Change in response direction**

- Large response to ppb concentrations
- Response and recovery times are long
- Device is initially n-type due to interaction with SiC
- > n-p type transition occurs upon prolonged NO₂ exposure
- > NO₂ adsorbed on surface withdraws electrons and increases resistance for n-type graphene
- > Hole dopes and reduces resistance for p-type graphene



Controlling the graphene uniformity and the unintentional charge transfer from SiC





Experimental: Scanning Kelvin probe microscopy – work function mapping

Nanoscale mapping of graphene thickness uniformity and doping



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1. Cantilever measures surface topography on first

2. Cantilever ascends to lift scan height.

3. Cantilever follows stored surface topography at the lift height above sample while responding to electric influences on second (interleave) scan.

Resulting maps show morphology and local variations in graphene work function



 $\rightarrow \Delta \Phi$ between 1LG and 2LG allows nanoscale mapping of graphene thickness

Eriksson et. Al., Applied Physics Letters 100 (2012) 24160





Monolayer coverage vs. terrace width

Mono layer uniformity depends on terrace width

□Substrate polytype and doping for **hexagonal SiC** (ntype 6H-SiC or SI 4H-SiC) do not significantly influence uniformity or graphene doping

□3C-SiC – higher 1LG % for lower terrace width, 1LG % independent on terrace width



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Eriksson et. Al., Applied Physics Letters 100 (2012) 24160

 Φ_{11G} vs. terrace width



Variations in ϕ_{1LG} follow variations in Ns:

3C-SiC: Lower doping, doping independent on terrace width



NO₂ sensing, single or double layer graphene?





SKPM in controlled environment





The probe is placed in an environmental chamber:

Controlled gas- or vacuum environment

➢ Visualization of how different chemical doping affects the electronic properties of individual 1LG and 2LG domains



Different shifts for 1LG and 2LG?



Mapping work function change with environment



Different shifts for 1LG and 2LG?

Physical Rev. B 83, 235434 (2011)

Different band structures

- Linear energy dispersion for 1LG
- More parabolic for 2LG ٠



R. Pearce, J. Eriksson, T. Iakimov, L. Hultman, A. Lloyd Spetz and R. Yakimova, ACS nano, accepted

NO₂ adsorption on single and double layer graphene



From 1-2L ΔV_{CPD}: Non-invasive measurement of substrate induced carriers

(1)
$$\delta n \ 1\text{LG} = \frac{e \ \partial V_{CPD} \ 2\sqrt{n}}{\hbar v_F \sqrt{\pi}}$$

R. Pearce, J. Eriksson, T. Iakimov, L. Hultman, A. Lloyd Spetz and R. Yakimova, ACS nano, accepted





(2)
$$\delta n \ 2LG = \frac{\delta V_{CPD} \ e \ 2m^*}{\hbar^2 \pi}$$

Conclusion

- Sensing with epitaxial graphene promising, ppb level NOx detection
- Obstacles: selectivity, response time, reproducibility
- Solutions: decoration with nanostructures, cleaning cycles, T cycles, FET
- Combustion engine NOx sensing: detection limit of 5 ppm, T90 = few seconds
 strong improvements in response time required
- NOx sensing in living environments: ppb level detection limit, T90 not crucial

 a likely application





